

J3 112. (Amended) The display device according to claim 110, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

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J4 115. (Amended) The display device according to claim 113, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

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J5 118. (Amended) The display device according to claim 116, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

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J6 121. (Amended) The display device according to claim 119, wherein the laser annealing is performed to crystallize an amorphous semiconductor layer in order to obtain a crystalline semiconductor layer.

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